

Features

- DC to 6000 MHz
- 16.2 dB Gain at 1000 MHz
- 13.5 dBm Output P1dB at 1000 MHz
- 28 dBm Output IP3 at 1000 MHz
- 3.2 dB Noise Figure at 2000 MHz

Applications

- Broadband Gain Blocks
- High Linearity Amplifiers

Packages Available

- (-B) SOT-89
- (-C) 85 Mil Micro-X

Description

The ECG004 is a high reliability, high linearity, low cost broadband amplifier, optimized for commercial communications. The device is manufactured using in-house developed, advanced Indium Gallium Phosphide Heterojunction Bipolar Transistor (InGaP HBT) technology and is designed for use as a 50 Ohm gain block. The amplifier features excellent VSWR, low noise figure and highly linear performance. Typical OIP3 is +28dBm at 1000MHz. The ECG004 operates from a single voltage supply and requires only two DC-blocking capacitors, a bias resistor and an inductor for operation. The device is ideal for wireless applications and is available in a low cost, surface-mountable plastic 85 mil Micro-X and SOT-89 packages. The ECG004 is designed in the Darlington configuration with direct feedback. Its operation frequency at low end is limited only by the dc blocking capacitor and the RF choke inductor (large values are required in both cases).

Electrical Specifications

Test Conditions: $I_c = 35 \text{ mA}$, $T_a = 25^\circ\text{C}$

SYMBOL	PARAMETER		LIMITS			UNIT	TEST CONDITION
			MIN.	TYP.	MAX.		
F	Frequency		DC		6000	MHz	
G	Gain (Small Signal)	f = 1000MHz f = 2000MHz f = 3000MHz f = 6000MHz		16.2 15.5 14.0 9.9		dB	
G	Gain (Large Signal)	f = 2000MHz	13	14.8		dB	Note 2
P _{1dB}	Output Power @ 1dB Compression	f = 1000MHz f = 2000MHz f = 3000MHz		13.5 13.0 12.8		dBm	
OIP3	Output Third Order Intercept	f = 1000MHz f = 2000MHz f = 3000MHz		28.0 27.0 26.0		dBm	Note 1
RL _{in}	Input Return Loss, 50 Ohm	f = 2000MHz		20.0		dB	
RL _{out}	Output Return Loss, 50 Ohm	f = 2000MHz		18.0		dB	
NF	Noise Figure	f = 2000MHz		3.2		dB	
V _{de}	Device Voltage		3.1	3.4	3.7	V	
Note 1: OIP3 = P _{out} (by power meter, total 2-tone power) + (IM3(dB))/2) - 3dB							
Note 2: Pin = - 0.2dBm (Gain at 1dB compression)							



CAUTION!
SENSITIVE ELECTRONIC DEVICE

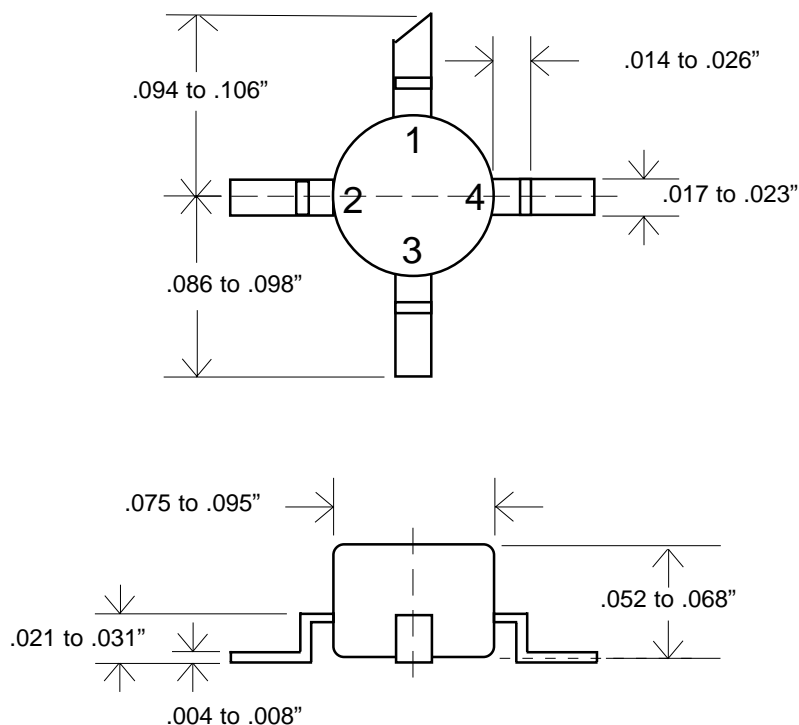
Absolute Maximum Ratings

Device Current	150	mA
RF Power Input	12	dBm
Operating Temperature	-40 to +85	°C
Storage Temperature	-65 to +150	°C
Junction Temperature	+200	°C

Note: Exceeding any of the absolute maximum ratings may cause permanent damage to the device.

Micro-X Package Outline

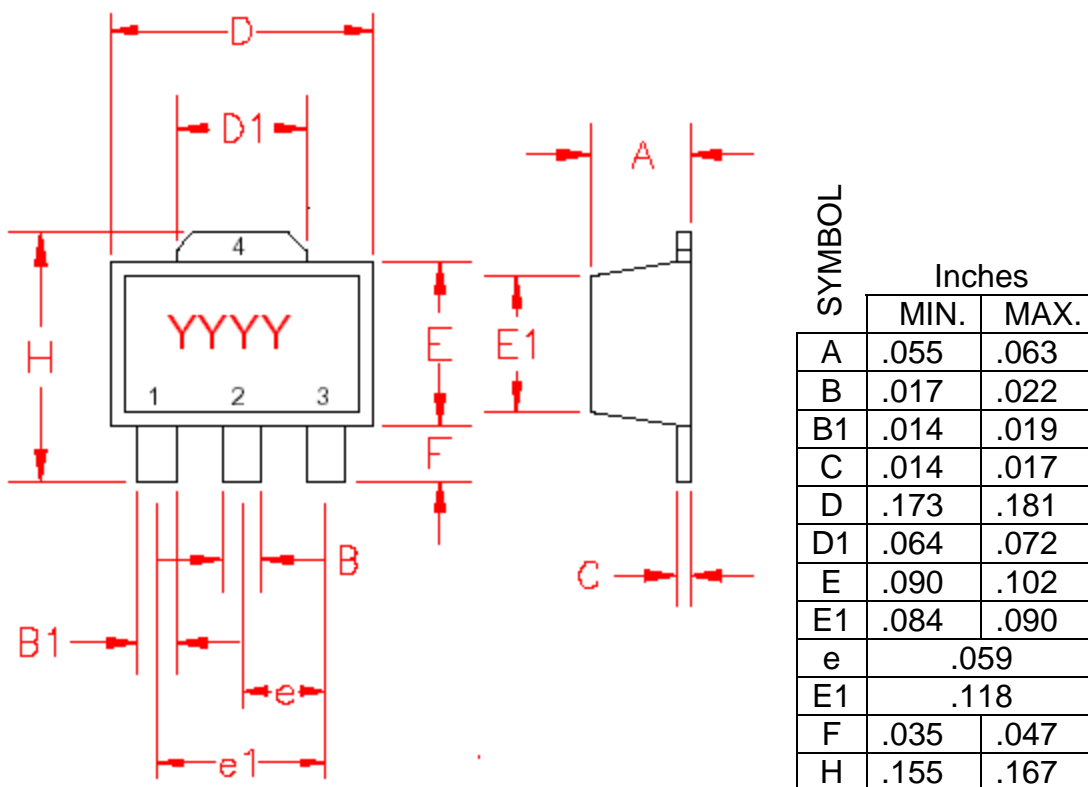
(all units are in inches)

**Pin Definitions**

Pin #	Pin	Definition
1	RFin	This pin has a nominal 50 ohm input impedance. It requires a DC blocking capacitor large enough to handle the lowest frequency used.
2, 4	Gnd	The two ground connections should be directly connected together to the ground plane on the PCB. The ground connection also serves as a heatsink.
3	RFout	This pin has a nominal 50 ohm output impedance. It requires a DC bias of 35mA through a series inductor and a resistor. A bypass capacitor (1.0 micro Farad) on the DC side of the inductor is recommended for providing instantaneous current during a modulated RF signal. Use a DC blocking capacitor on the output with similar requirements as the input side.

SOT-89 Package Outline

(all units are in inches)



Pin Definitions

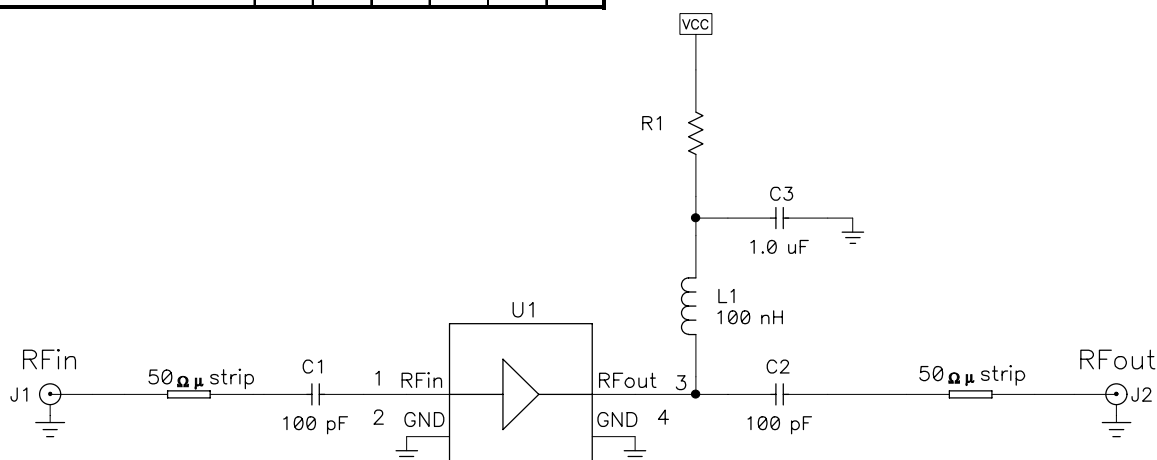
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Evaluation Board Schematic SOT-89 and Micro-X

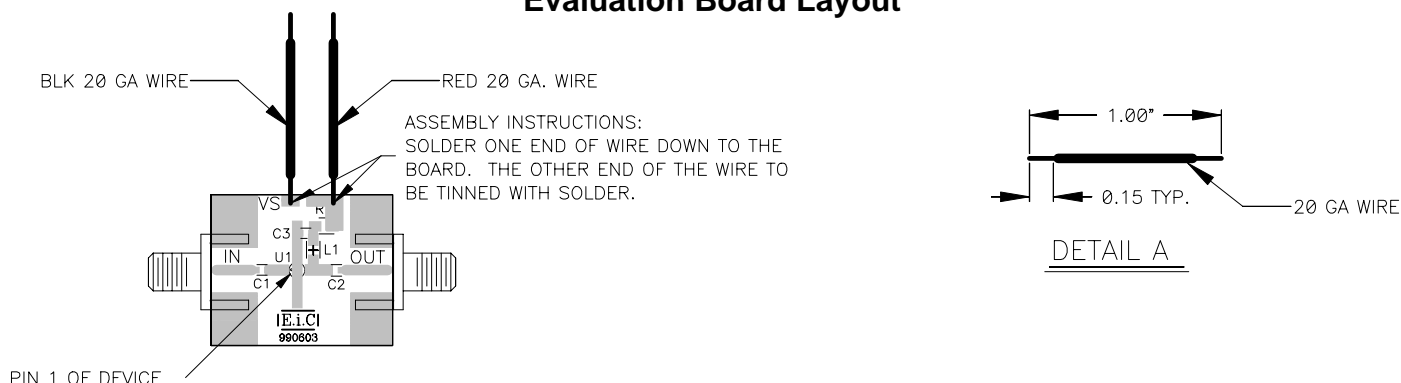
Recommended Bias Resistor Values

$$R = (V_{cc} - V_{de}) / I_{cc} = (V_{cc} - 3.4) / 0.035$$

Approximate Supply Voltage (V_{cc}) based on standard values for R1	5	6	7	8	9	10
R1 (Ohms)	47	75	100	130	160	180



Evaluation Board Layout



Evaluation Board Materials

QTY	DESIGNATOR	VALUE	DESCRIPTION	MANUFACTURER & P/N
2	C1, C2	100pF	CAPACITOR, 0603	MARUWA CE101J1NO
1	C3	1.0uF	CAPACITOR, 0603	MARUWA CE105K1NR
1	R1	75 Ω	RESISTOR, 0603	ROHM MCR03J750
1	L1	100 nH	INDUCTOR, 0805	TOKO LL2012-FR10K
2	J1, J2		SMA CONNECTOR	EF JOHNSON 142-0701-881
1		---	IC, ECG004	EiC Corp
RED		---	20 GA, WIRE 1.0"	ANY
BLACK		---	20 GA, WIRE 1.0"	ANY
		---	PCB	EiC Corp 60-000009-003B

NOTE 1

NOTE 1

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SEE
DETAIL A

SEE
DETAIL A

1. EIC RECOMMENDED COMPONENTS ARE SHOWN. EQUIVALENT COMPONENTS MAY BE USED.

2. LARGER VALUES GIVE BETTER LOW FREQUENCY RESPONSE (<500 MHz)

NOTES: UNLESS OTHERWISE SPECIFIED

Figure 1

V_{de} vs. I_{cc}
(IC Tested on Eval Board)

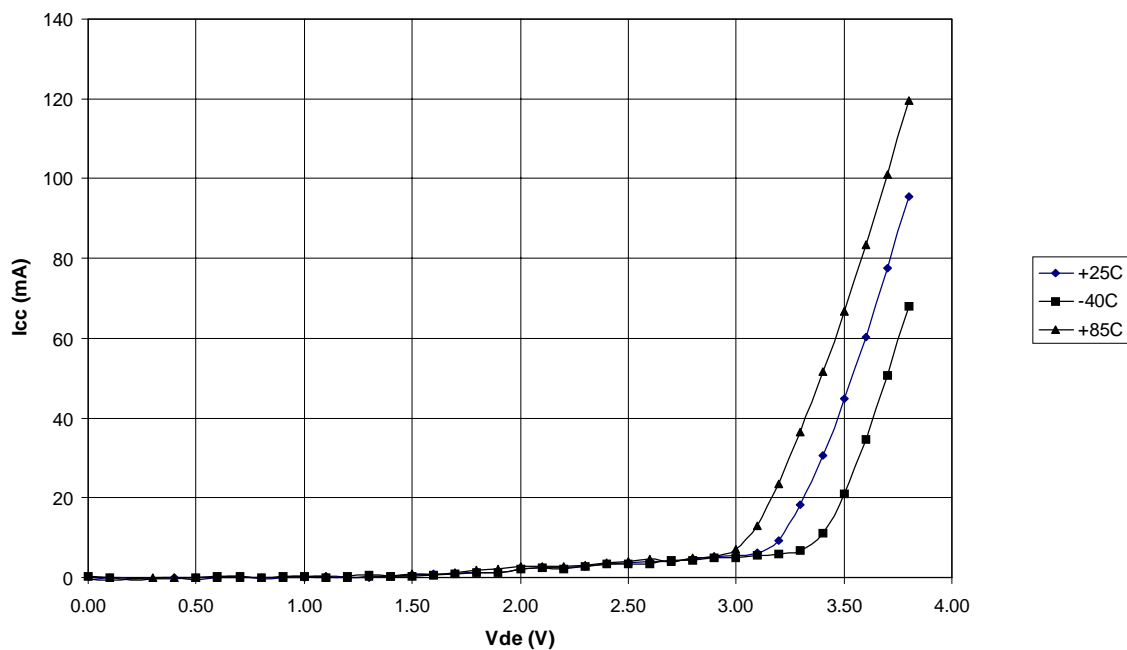


Figure 2

P_{1dB} vs. Frequency
(IC Tested on Eval Board)

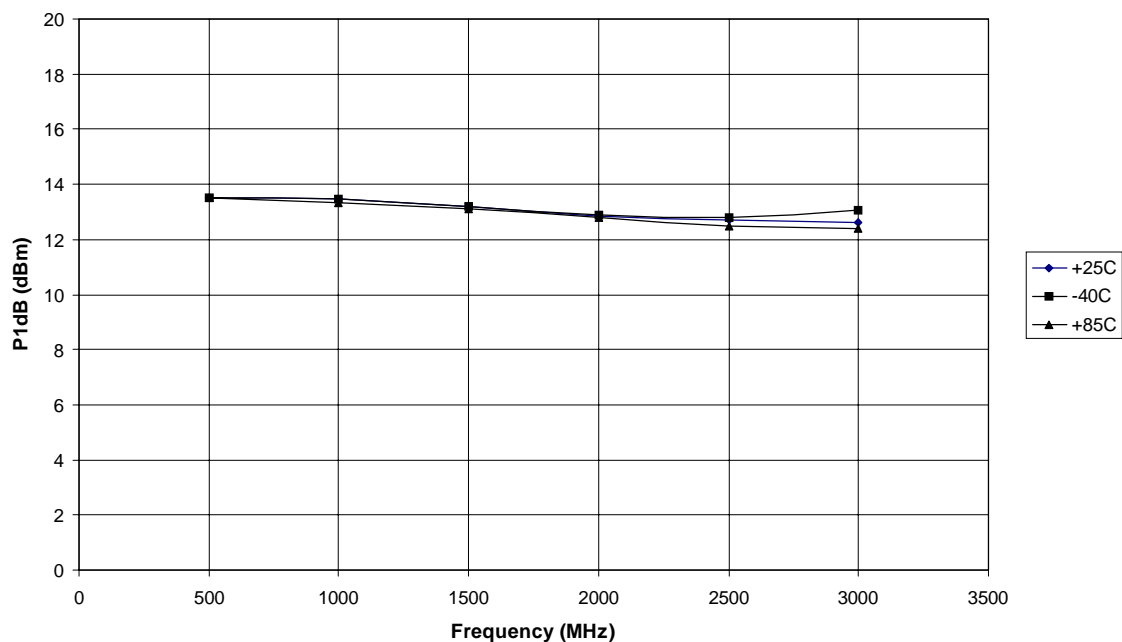


Figure 3

Gain vs. Frequency

(IC Tested on Eval Board)

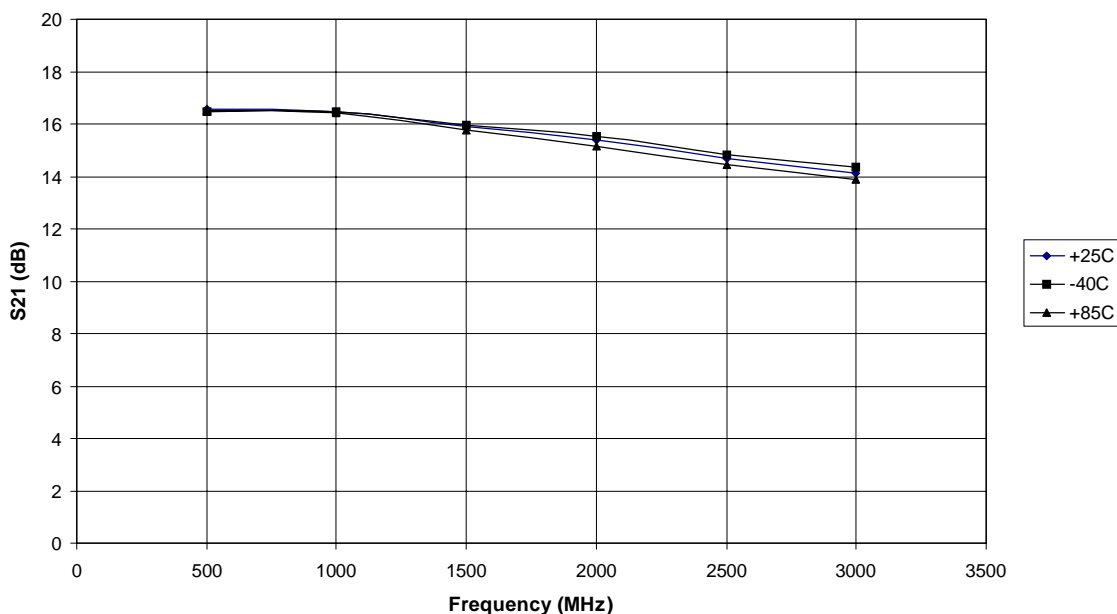


Figure 4

Gain vs. Frequency, T=25 degree C

(IC Tested in a 50 Ohm Fixture)

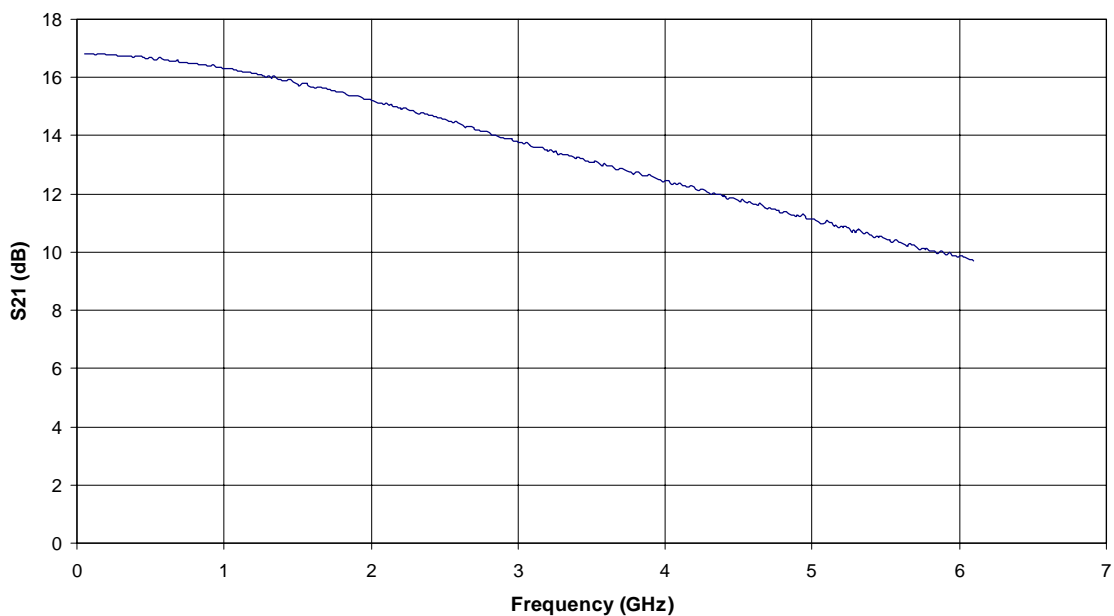


Figure 5

S11, S22 vs. Frequency, T=25 degree C

(IC Tested in a 50 Ohm Fixture)

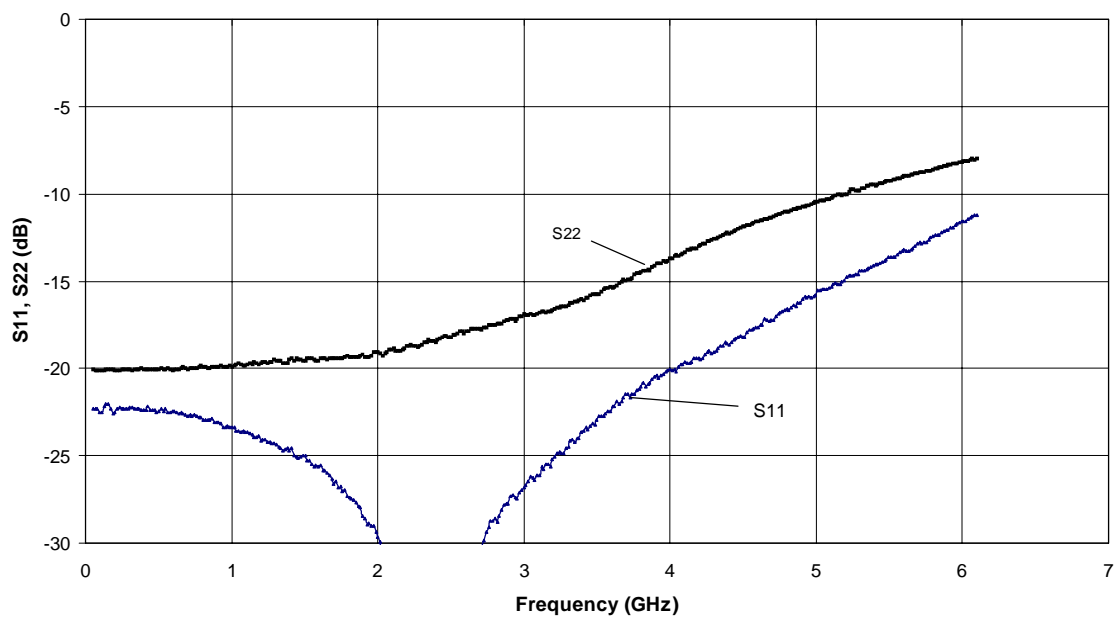


Figure 6

Reverse Isolation vs. Frequency, T=25 degree C

(IC Tested in a 50 Ohm Fixture)

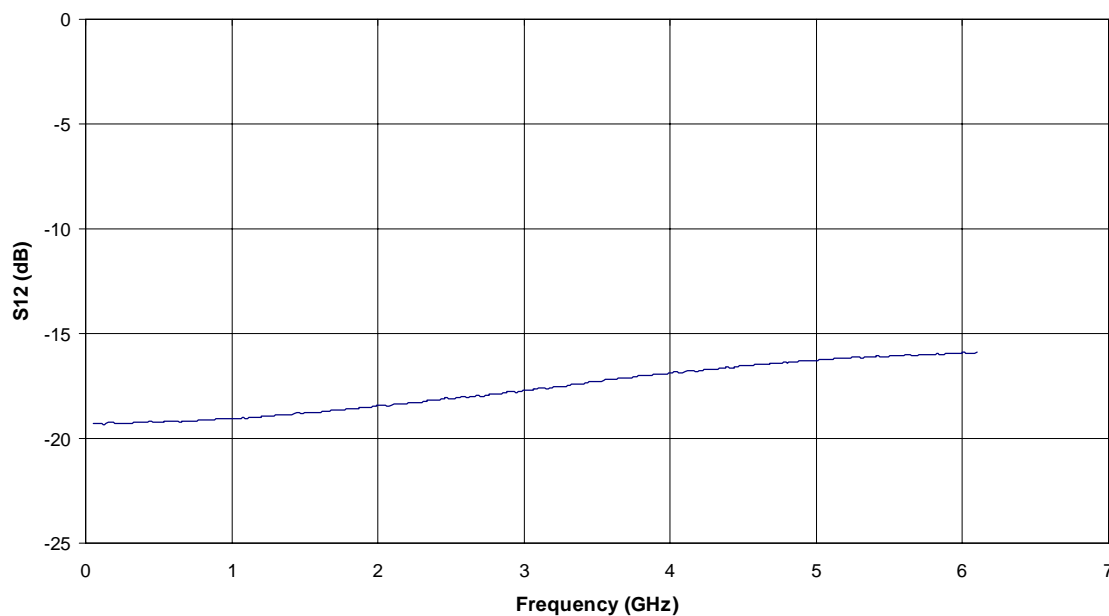


Figure 7

OIP3 vs. Frequency
(IC Tested on Eval Board)

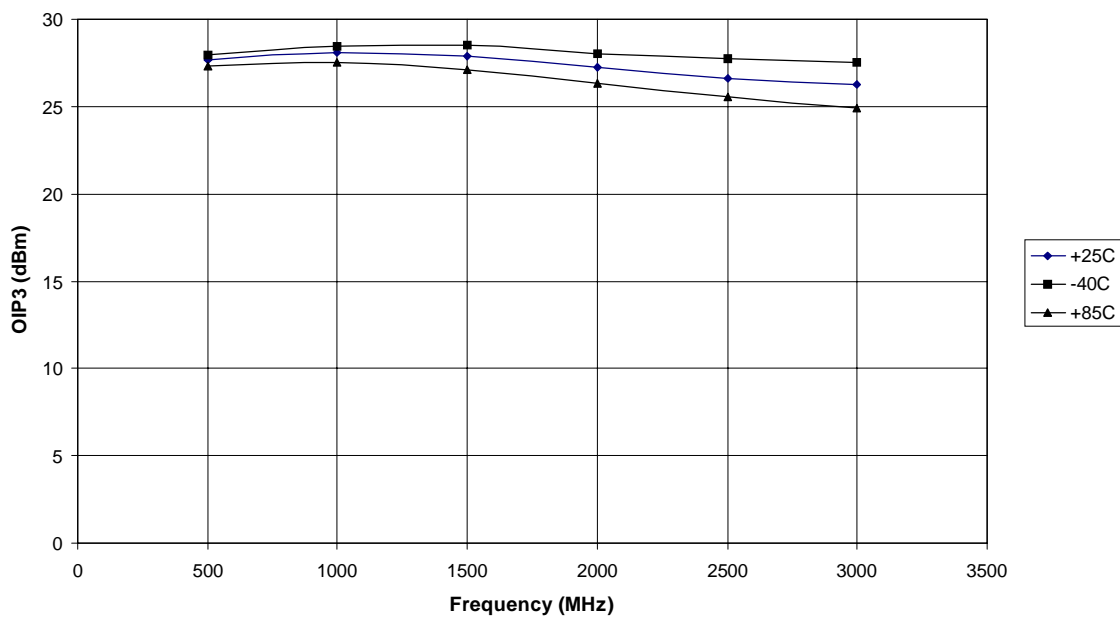
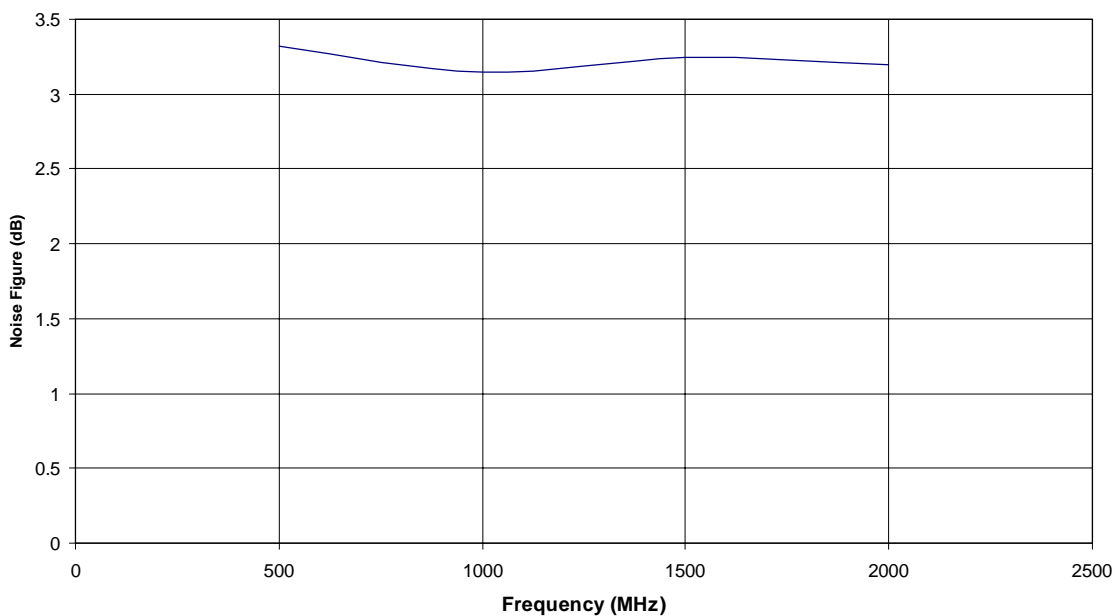


Figure 8

Noise Figure vs. Frequency
(IC Tested on Eval Board)



APPLICATION NOTES

Please visit our website at www.eiccorp.com to view or download the following documents.
You may also call our Customer Service to request a hardcopy.

Document #	Description
AP-000192-000	Discussion of Technology and Reliability Enhancements
AP-000194-000	Biasing and Performance Enhancements
AP-000487-000	Tape and Reel Specifications and Package Drawings
AP-000515-000	Voltage Spike Suppression
AP-000516-000	Application Note Index